ABSTRACT OF THE DISCLOSURE

A method of correcting a mask pattern for manufacturing a semiconductor device is disclosed. With this correcting method, a portion where a line portion overlaps a contact portion is extracted, the space width from the overlapped portion to another line portion adjoining this overlapped portion and the line width of the line portion are extracted, dependency of the line width variation amount of the line portion generated after wafer process and the space width is obtained, the dependency is divided per design grid width, an intersection between this design grid width and the dependency, the relationship is divided per intersection part, and a correction rule table is made for making a correction of integer times of the design grid width per the intersection part. And a correction of integer times of the design grid width is made based on the correction rule table to the overlapped portion.

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